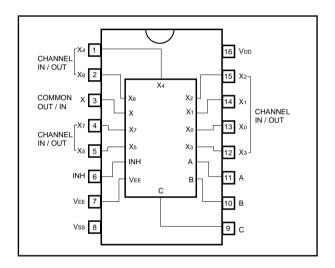
# 8-channel analog multiplexer / demultiplexer BU4051BC / BU4051BCF / BU4051BCFV

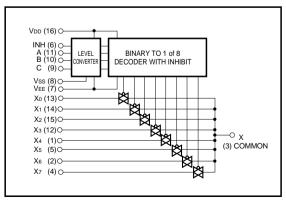
The BU4051BC, BU4051BCF and BU4051BCFV are analog multiplexers / demultiplexers which use three-input digital signals for control via an 8-channel analog switch.

These products feature high on / off output voltage ratio and low crosstalk between analog switches.

### Block diagram



### Logic circuit diagram



### Truth table

| INH | Α | В | С | ON SWITCH      |
|-----|---|---|---|----------------|
| L   | L | L | L | <b>X</b> 0     |
| L   | Н | L | L | X <sub>1</sub> |
| L   | L | Н | L | X <sub>2</sub> |
| L   | Н | Н | L | Х3             |
| L   | L | L | Н | X4             |
| L   | Н | L | Н | <b>X</b> 5     |
| L   | L | Н | Н | X <sub>6</sub> |
| L   | Н | Н | Н | X <sub>7</sub> |
| Н   | Х | Х | Х | NONE           |
|     |   |   |   |                |

X: Irrelevant



# ●Absolute maximum ratings (Ta = 25°C)

| Parameter              | Symbol          | Limits                            | Unit |
|------------------------|-----------------|-----------------------------------|------|
| Power supply voltage 1 | V <sub>DD</sub> | − 0.5 ~ <b>+</b> 20               | V    |
| Power supply voltage 2 | VDD-VEE         | - 0.5 ~ <b>+</b> 20               | V    |
| Power dissipation      | Pd              | 1000 (DIP), 500 (SOP), 400 (SSOP) | mW   |
| Operating temperature  | Topr            | - 40 ~ + 85                       | °C   |
| Storage temperature    | Tstg            | – 55 ~ + 150                      | °C   |
| Input voltage          | Vin             | - 0.5 ~ Vpp + 0.5                 | V    |

# •Electrical characteristics

DC characteristics (unless otherwise noted, Ta = 25°C, VEE = Vss = 0V)

| Parameter                   | Symbol | Min. | Тур. | Max.  | Unit | V <sub>DD</sub> (V) |                       |  |
|-----------------------------|--------|------|------|-------|------|---------------------|-----------------------|--|
|                             |        | 3.5  |      |       |      | 5                   |                       |  |
| Input high-level voltage    | ViH    | 7.0  |      | _     | V    | 10                  | _                     |  |
| 1                           |        | 11.0 | _    | _     |      | 15                  |                       |  |
|                             |        | _    | _    | 1.5   |      | 5                   |                       |  |
| Input low-level voltage     | VIL    | _    | _    | 3.0   | V    | 10                  | _                     |  |
|                             |        | _    | _    | 4.0   |      | 15                  |                       |  |
| Input high-level current    | Іін    | _    | _    | 0.3   | μΑ   | 15                  | V <sub>IH</sub> = 15V |  |
| Input low-level current     | lı∟    | _    | _    | - 0.3 | μΑ   | 15                  | VIL = 0V              |  |
|                             | Ron    | _    | _    | 950   | Ω    | 5                   | VIN = VDD / 2         |  |
| RON resistance              |        | _    | _    | 250   |      | 10                  |                       |  |
|                             |        | _    | _    | 160   |      | 15                  |                       |  |
| RON resistance deflexion    | ΔRon   |      | 10   | _     | Ω    | 5                   | _                     |  |
|                             |        |      | 6    | _     |      | 10                  |                       |  |
|                             |        | -    | 4    | _     |      | 15                  |                       |  |
| OFF-channel leakage current | loff - | _    | _    | 0.3   | μΑ   | 15                  | _                     |  |
|                             |        | _    | _    | - 0.3 |      | 15                  |                       |  |
|                             | lod    | _    | _    | 5     | μΑ   | 5                   | Vi = VDD or GND       |  |
| Static current dissipation  |        | _    | _    | 10    |      | 10                  |                       |  |
|                             |        | _    | _    | 15    |      | 15                  |                       |  |

Switching characteristics (unless otherwise noted, Ta = 25°C, VEE = VSS = 0V, RL = 1k $\Omega$ , CL = 50pF)

| Parameter                                | Symbol                   | Min. | Тур. | Max. | Unit - | Conditions          |              | Measurement |
|--|--------------------------|------|------|------|--------|---------------------|--------------|-------------|
|  |                          |      |      |      |        | V <sub>DD</sub> (V) | Conditions   | circuit     |
| Propagation delay time<br>CHANNEL IN→OUT | tplн<br>tpнl             | _    | 15   | 45   | ns     | 5                   | _            | Fig.4       |
|  |                          | _    | 8    | 20   |        | 10                  |              |             |
|  |                          | _    | 6    | 15   |        | 15                  |              |             |
|  | tpнz, tplz<br>tpzн, tpzl | _    | 170  | 550  | ns     | 5                   | _            | Fig.5, 6    |
| Propagation delay time<br>CONT→OUT       |                          | _    | 90   | 240  |        | 10                  |              |             |
|  |                          | _    | 70   | 160  |        | 15                  |              |             |
|  | tpнz, tplz<br>tpzн, tpzl | _    | 150  | 380  | ns     | 5                   | _            | Fig.5, 6    |
| Propagation delay time INHIBIT→OUT       |                          | _    | 70   | 200  |        | 10                  |              |             |
|  |                          | _    | 50   | 160  |        | 15                  |              |             |
| Max. propagation frequency               | f <sub>Max</sub> .       | _    | 20   | _    | MHz    | 5                   | VEE = - 5V*1 | Fig.7       |
| Feedthrough                              | FT                       | _    | 0.5  | _    | MHz    | 5                   | VEE = - 5V*2 | Fig.7       |
| Sinewave distortion                      | D                        | _    | 0.02 | _    | %      | 5                   | VEE = - 5V*3 | Fig.7       |
| Input capacitance (control)              | Cc                       | _    | 5    | _    | pF     | _                   | _            | _           |
| Input capacitance (switch)               | Cs                       |      | 10   | _    | pF     | _                   |              |             |

 $<sup>\</sup>pm 1 \text{ Vin} = 5 \text{VP-P}$  sine wave, frequency that enables 20 log10 VoUT / Vin = -3 dB

### Measurement circuits

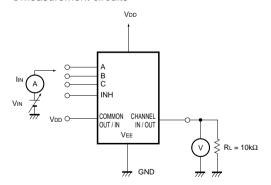


Fig. 1 Input voltage, current

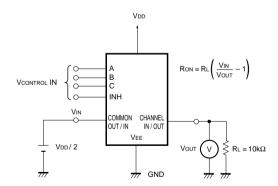


Fig. 2 ON resistance, ON resistance deviation

 $<sup>*2 \</sup>text{ VIN} = 5 \text{VP-P}$  sine wave, frequency that enables 20 log10 VoUT / VIN = -50 dB at Channel off

<sup>\*3</sup> VIN = 5VP-P sine wave

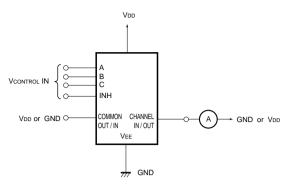


Fig. 3 OFF-channel leakage current

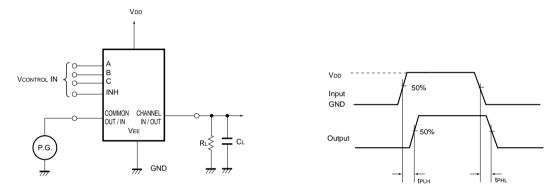


Fig. 4 Propagation delay time (Switch IN to OUT)

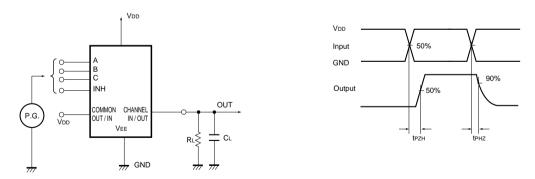


Fig. 5 Propagation delay time (CONT, INH to OUT)

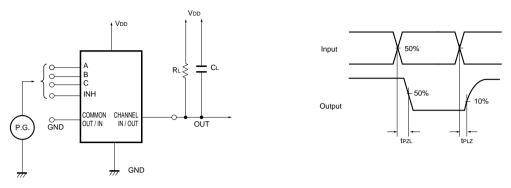


Fig. 6 Propagation delay time (CONT, INH to OUT)

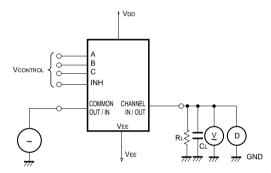


Fig. 7 Maximum propagation frequency, feedthrough attenuation, sine wave distortion

### •Electrical characteristic curve

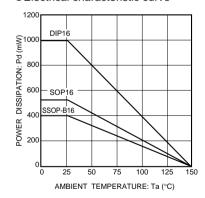
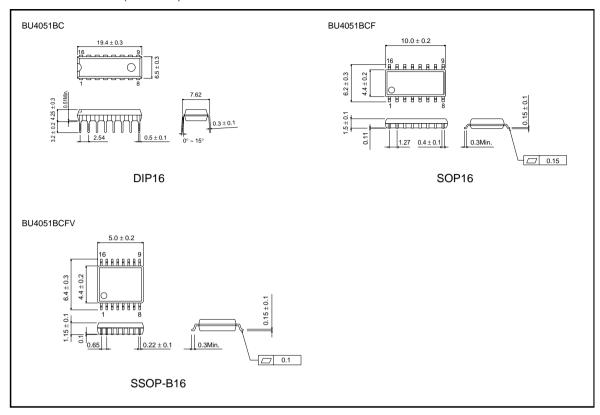


Fig. 8 Power dissipation vs. ambient temperature

# External dimensions (Units: mm)



### **Notes**

- No technical content pages of this document may be reproduced in any form or transmitted by any
  means without prior permission of ROHM CO.,LTD.
- The contents described herein are subject to change without notice. The specifications for the
  product described in this document are for reference only. Upon actual use, therefore, please request
  that specifications to be separately delivered.
- Application circuit diagrams and circuit constants contained herein are shown as examples of standard
  use and operation. Please pay careful attention to the peripheral conditions when designing circuits
  and deciding upon circuit constants in the set.
- Any data, including, but not limited to application circuit diagrams information, described herein are intended only as illustrations of such devices and not as the specifications for such devices. ROHM CO.,LTD. disclaims any warranty that any use of such devices shall be free from infringement of any third party's intellectual property rights or other proprietary rights, and further, assumes no liability of whatsoever nature in the event of any such infringement, or arising from or connected with or related to the use of such devices.
- Upon the sale of any such devices, other than for buyer's right to use such devices itself, resell or
  otherwise dispose of the same, no express or implied right or license to practice or commercially
  exploit any intellectual property rights or other proprietary rights owned or controlled by
- ROHM CO., LTD. is granted to any such buyer.
- Products listed in this document use silicon as a basic material.
   Products listed in this document are no antiradiation design.

The products listed in this document are designed to be used with ordinary electronic equipment or devices (such as audio visual equipment, office-automation equipment, communications devices, electrical appliances and electronic toys).

Should you intend to use these products with equipment or devices which require an extremely high level of reliability and the malfunction of with would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), please be sure to consult with our sales representative in advance.

About Export Control Order in Japan

Products described herein are the objects of controlled goods in Annex 1 (Item 16) of Export Trade Control Order in Japan.

In case of export from Japan, please confirm if it applies to "objective" criteria or an "informed" (by MITI clause) on the basis of "catch all controls for Non-Proliferation of Weapons of Mass Destruction.

